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— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

[Continued on next page]

(54) **Title**: ARRANGEMENTS AND METHODS FOR IMPROVING BEVEL ETCH REPEATABILITY AMONG SUBSTRATES

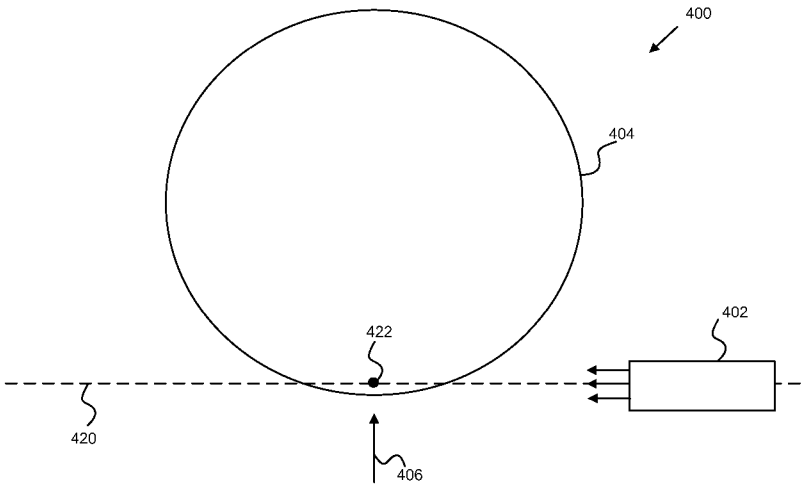


FIG. 4A

(57) **Abstract**: A method, performed in connection with bevel etching of a substrate, for improving bevel- etch repeatability among substrates, is disclosed. The method includes providing an optical arrangement and ascertaining at least one bevel edge characteristic of a bevel edge of said substrate. The method also includes deriving at least one compensation factor from said at least one bevel edge characteristic, said at least one compensation factor pertaining to an adjustment in a bevel etch process parameter. The method further includes performing said bevel etching utilizing said at least one compensation factor.

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